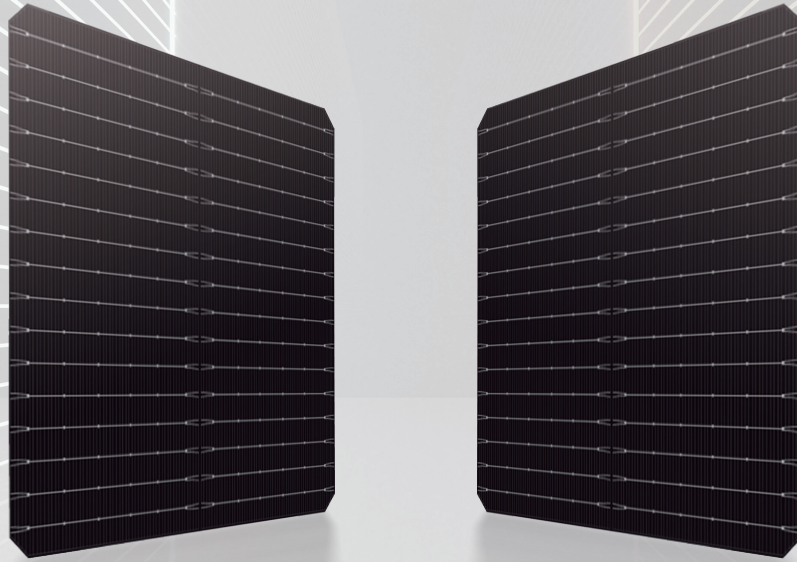


SYCN191T1638

N-TOPCon



Highlight



高转换效率:
正面效率 $\geq 26\%$; 双面率 $\geq 80\%$



N型单晶硅片:
低衰退; 无光致衰减



低温度系数:
功率温度系数 $\geq -0.29\%/^{\circ}\text{C}$



低封装损失:
更适合高效组件



抗PID:
优越的抗PID性能



弱光响应强:
200 W/m²弱光下相对转换效率 $\geq 97\%$

产品特征:

产品型号: SYCN191T1638 尺寸规格: 191.6 \times 182.2 \pm 0.25mm, Φ 256 \pm 0.35mm

电池厚度: 130 \pm 15 μm 正面: 16BB 背面: 16BB



The TUV certificate holder is Sany Silicon Energy (Zhuzhou) Co., Ltd.
Made in China

Version: SYMN202311 Specifications included in this manual are subject to change without notice.

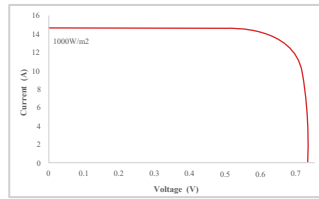
温度系数

电流温度系数 (%/°C)	+0.046
电压温度系数 (%/°C)	-0.26
功率温度系数 (%/°C)	-0.29

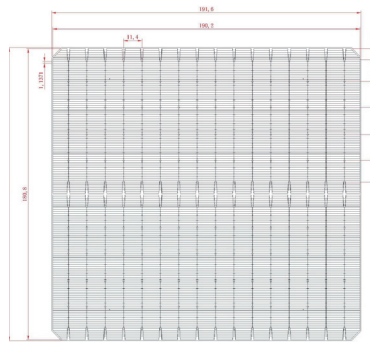
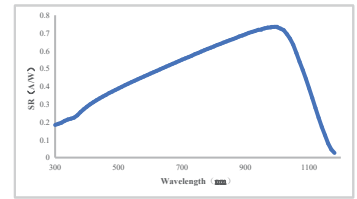
产品特征

尺寸规格	191.6×182.2±0.25mm, Φ256±0.35mm
电池厚度	130±15μm
正面(+)	氮化硅, 0.018mm主栅宽度, 16根主栅, 160根细栅
背面(-)	氮化硅, 0.018mm主栅宽度, 16根主栅, 190根细栅

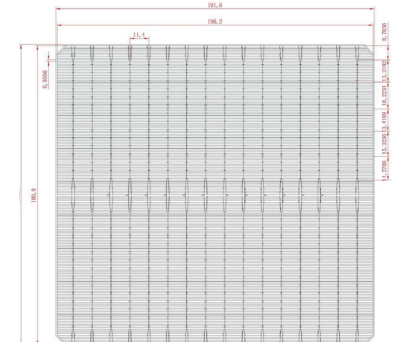
IV-曲线



光谱响应



电池正面



电池背面

电性能特征

Eff(%)	Pmpp(W)	I _{mp} (A)	V _{mp} (V)	V _{oc} (V)	I _{sc} (A)	FF(%)
26.5	9.22	13.835	0.6666	0.7313	14.569	86.56
26.4	9.19	13.845	0.6636	0.7301	14.561	86.42
26.3	9.15	13.806	0.6629	0.7290	14.565	86.20
26.2	9.12	13.829	0.6593	0.7284	14.561	85.96
26.1	9.08	13.818	0.6574	0.7274	14.555	85.79
26.0	9.05	13.752	0.6581	0.7266	14.547	85.62
25.9	9.02	13.748	0.6559	0.7262	14.555	85.32
25.8	8.98	13.735	0.6539	0.7258	14.554	85.03
25.7	8.95	13.711	0.6531	0.7256	14.544	84.85
25.6	8.93	13.707	0.6515	0.7252	14.545	84.66
25.5	8.89	13.654	0.6510	0.7247	14.546	84.33
25.4	8.85	13.703	0.6455	0.7242	14.557	83.91
25.3	8.81	13.652	0.6455	0.7237	14.543	83.73
25.2	8.79	13.704	0.6418	0.7230	14.540	83.66
25.1	8.74	13.674	0.6395	0.7228	14.533	83.25
25.0	8.73	13.666	0.6387	0.7225	14.529	83.15
24.9	8.68	13.674	0.6349	0.7199	14.520	83.06
24.8	8.65	13.671	0.6325	0.7197	14.506	82.83

